

We are so pleased to announce the recipients of AM-FPD '16 Award.

They will be presented the award in the Opening Session of AM-FPD '17 on **July 4, 2017**.

AM-FPD '16 Best Paper Award

- 7-3 **Comparative Study on Light-Induced Negative-Bias Stress Stabilities in Amorphous In-Ga-Zn-O Thin Film Transistors with Photoinduced Transient Spectroscopy**

Kazushi Hayashi, Mototaka Ochi, Aya Hino, Hiroaki Tao, Hiroshi Goto, Toshihiro Kugimiya, *Kobe Steel, Ltd., Japan*

Paper Award

- L-1 **Charge Effects of Ultrafine FET with Nanodot Type Floating Gate**

Takahiko Ban¹, Shinji Migita², Yukiharu Uraoka³, Shinichi Yamamoto^{1, 1}, *Ryukoku Univ., Japan*,²*Nat'l Inst. of Advanced Industrial Sci. and Technol., Japan*,³*Nara Inst. of Sci. and Technol., Japan*

- 5-1 **Laser Deposition for the Controlled Co-Deposition of Organolead Halide Perovskite**

Tetsuhiko Miyadera, Takeshi Sugita, Hitoshi Tampo, Koji Matsubara, Masayuki Chikamatsu, *Nat'l Inst. of Advanced Industrial Sci. and Technol. (AIST), Japan*

AM-FPD '16 Poster Paper Award

- P-57 **Fully Printable Mesoscopic Perovskite Solar Cells; Effect of NiO Layer on the Device Performance**

Nirmal Peiris^{1,2}, Gai Mizuta¹, Hiroyuki Kanda¹, Tomoya Nishina¹, Seigo Ito², Hiroshi Segawa^{1, 1}, *The Univ. of Tokyo, Japan*,²*Univ. of Hyogo, Japan*

- P-43 **Study on Graphene Formation by Hot Mesh Deposition**

Satoshi Fuji, Akira Heya, Naoto Matsuo, *Univ. of Hyogo, Japan*

AM-FPD '16 Student Award

Yeo-Myeong Kim, *Kyung Hee Univ., Korea*

- 2-3 **Brain-Like Synaptic Operations of Thin-Film Transistors Using In-Ga-Zn-O Active Channel and PVP-SBA Electrolytic Gate Insulator**

AMFPD '16-ECS Japan Section Young Researcher Award

Keisuke Ide, *Tokyo Inst. of Technol., Japan*,

- 7-2 **Why High-Pressure Sputtering must be Avoided to Deposit a-In-Ga-Zn-O Films**